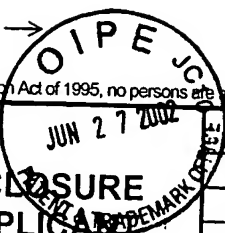


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## Complete if Known

Application Number	10/080,789
Filing Date	February 21, 2002
First Named Inventor	Staple, Bevan
Art Unit	2661
Examiner Name	Not Yet Known
Attorney Docket Number	019930-006100US

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## OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
ah	BC	AKIYAMA, TERUNOBU, et al., "Controlled Stepwise Motion in Polysilicon Microstructures," Journal of Microelectromechanical Systems, Vol. 2, No. 3, pp. 106-110, September 1993	
ah	BD	ASHRUF, C.M.A., et al., "Galvanic porous silicon formation without external contacts," Sensors and Actuators 74, pp. 118-122, 1999	
ah	BE	BEAN, KENNETH E., "Anisotropic Etching of Silicon," IEEE Transactions on Electron Devices, Vol. ED-25, No. 10, pp. 1185-1193, October 1978	
ah	BF	CIARLO, DINO R., "A latching accelerometer fabricated by the anisotropic etching of (110) oriented silicon wafers," IOP Publishing, Ltd., 1992	
ah	BG	KAAJAKARI, VILLE, et al., "Ultrasonic Actuation for MEMS Dormancy-Related Stiction Reduction," Proceedings of SPIE Vol. 4180, 2000	
ah	BH	KOCH, T., et al., "Anisotropically etched deep gratings for InP/InGaAsP Optical devices," J. Appl. Phys. 62 (8), October 1987	
ah	BI	SCHILLING, M., et al., "Deformation-free overgrowth of reactive ion beam etched submicron structures in InP by liquid phase epitaxy," Appl. Phys. Letter 49 (12) September 1986	
ah	BJ	TANG, WILLIAM C., et al., "Electrostatically Balanced Comb Drive for Controlled Levitation," Technical Digest IEEE Solid-State Sensor and Actuator Workshop, pp. 23-27, June 1990	
ah	BK	TORCHEUX, L., et al., "Electrochemical Coupling Effects on the Corrosion of Silicon Samples in HF Solutions," J. Electrochem. Soc. Vol. 142, No. 6, June 1995	
ah	BL	VAN KESSEL, PETER F. et al, "A MEMS-Based Projection Display," Proceedings of the IEEE, Vol. 86, No. 8, pp. 1687-1704, August 1998	
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ah	BN	KELLER, CHRISTOPHER GUILD, "Microfabricated Silicon High Aspect Ratio Flexures for In-Plane Motion," Dissertation, Fall 1998	

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